

MOSFET - Power, Single N-Channel, STD Gate, SO8FL

40 V, 3.9 mΩ, 80 A

NVMFWS4D0N04XM

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (5 x 6 mm) with Compact Design
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

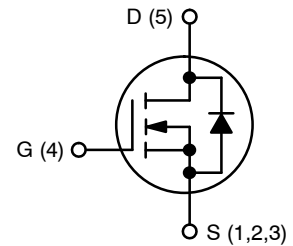
- Motor Drive
- Battery Protection
- Synchronous Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

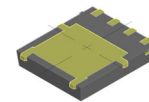
Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V _{DSS}	40	V
Gate-to-Source Voltage	DC	V _{GS}	±20	V
Continuous Drain Current	T _C = 25°C	I _D	80	A
	T _C = 100°C		57	
Power Dissipation	T _C = 25°C	P _D	43	W
Pulsed Drain Current	T _C = 25°C, t _p = 10 μs	I _D	450	A
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C
Source Current (Body Diode)		I _S	59	A
Single Pulse Avalanche Energy (I _{PK} = 3.6 A)		E _{AS}	138	mJ
Lead Temperature for Soldering Purposes		T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	3.9 mΩ @ 10 V	80 A



N-CHANNEL MOSFET



DFNW5 (SO-8FL)
CASE 507BA



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

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THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.5	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	$R_{\theta JA}$	42	

- Surface-mounted on FR4 board using 650 mm², 2 oz Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$. Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$			1	μA
		$V_{DS} = 40\text{ V}, T_J = 125^\circ\text{C}$			20	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}, T_J = 25^\circ\text{C}$		3.4	3.9	m Ω
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 30\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	2.5		3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 30\text{ }\mu\text{A}$		-7.36		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 6\text{ A}$		32		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		784		pF
Output Capacitance	C_{OSS}			504		
Reverse Transfer Capacitance	C_{RSS}			10		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DD} = 32\text{ V}, I_D = 6\text{ A}$		12		nC
Threshold Gate Charge	$Q_{G(TH)}$			2		
Gate-to-Source Charge	Q_{GS}			3		
Gate-to-Drain Charge	Q_{GD}			2		
Gate Resistance	R_G	$f = 1\text{ MHz}$		1.6		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 10\text{ V}, V_{DD} = 32\text{ V},$ $I_D = 6\text{ A}, R_G = 0\text{ }\Omega$		7		ns
Rise Time	t_r			8		
Turn-Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			9		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 6\text{ A}, T_J = 25^\circ\text{C}$		0.78	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 6\text{ A}, T_J = 125^\circ\text{C}$		0.63		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI/dt = 100\text{ A}/\mu\text{s},$ $I_S = 6\text{ A}, V_{DD} = 32\text{ V}$		53		ns
Charge Time	t_a			9		
Discharge Time	t_b			44		
Reverse Recovery Charge	Q_{RR}			18		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

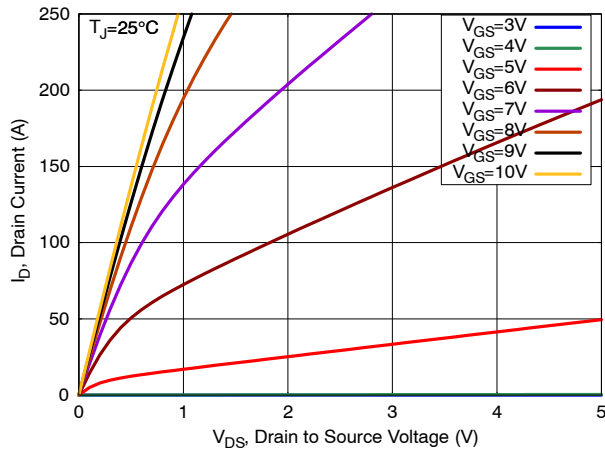


Figure 1. On-Region Characteristics

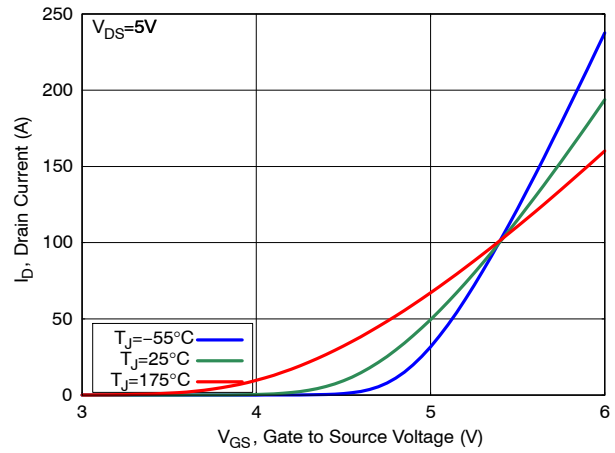


Figure 2. Transfer Characteristics

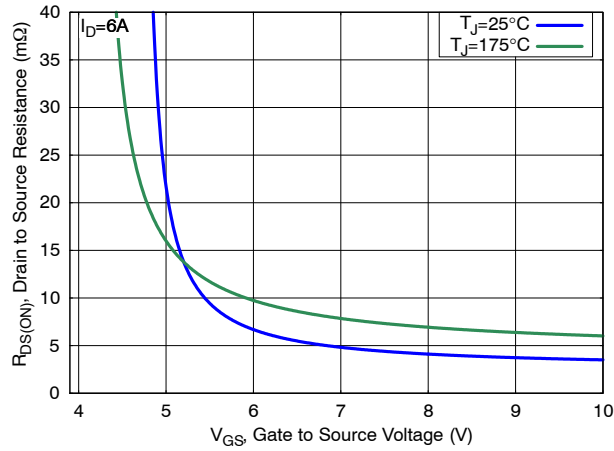


Figure 3. On-Resistance vs. Gate Voltage

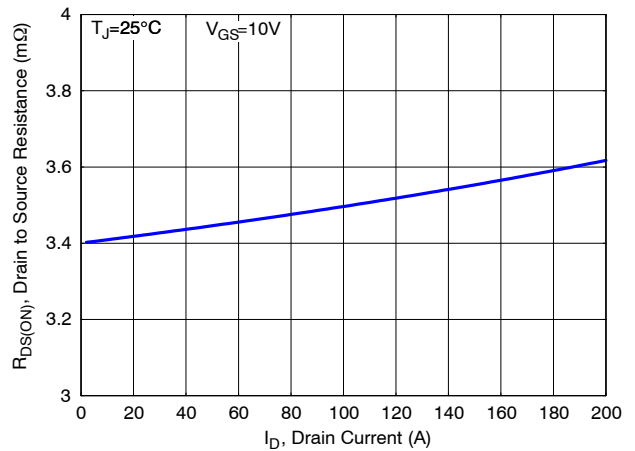


Figure 4. On-Resistance vs. Drain Current

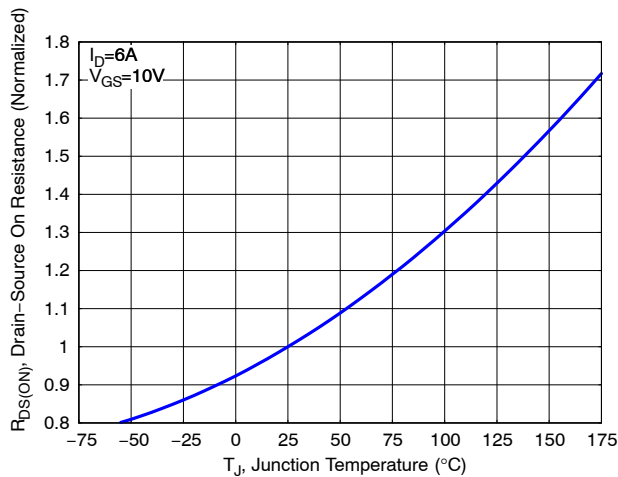


Figure 5. Normalized ON Resistance vs. Junction Temperature

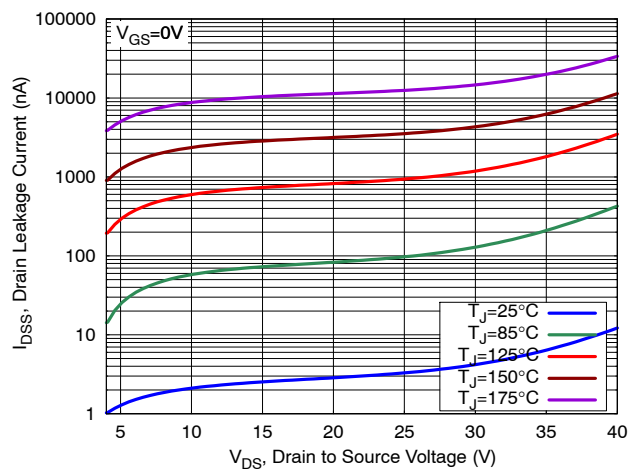


Figure 6. Drain Leakage Current vs. Drain Voltage

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TYPICAL CHARACTERISTICS (continued)

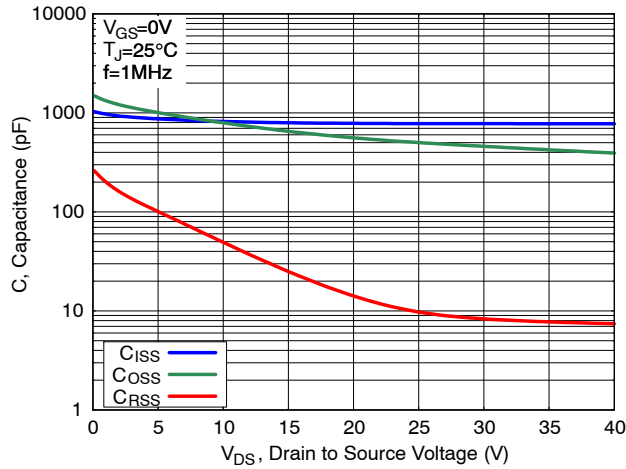


Figure 7. Capacitance Characteristics

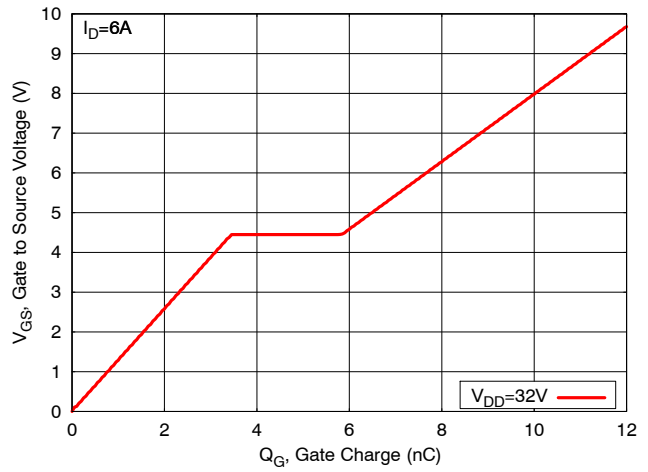


Figure 8. Gate Charge Characteristics

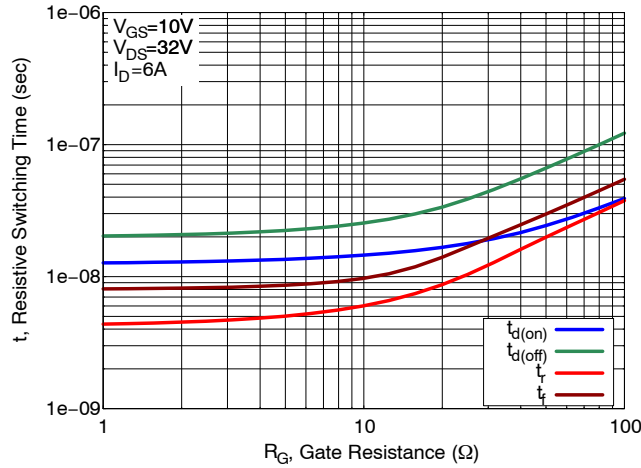


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

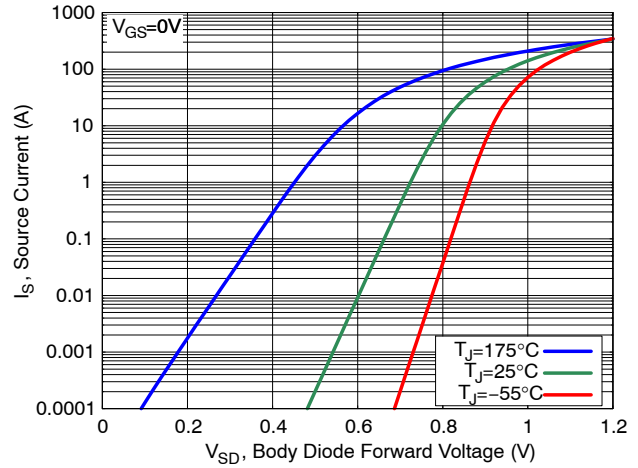


Figure 10. Diode Forward Characteristics

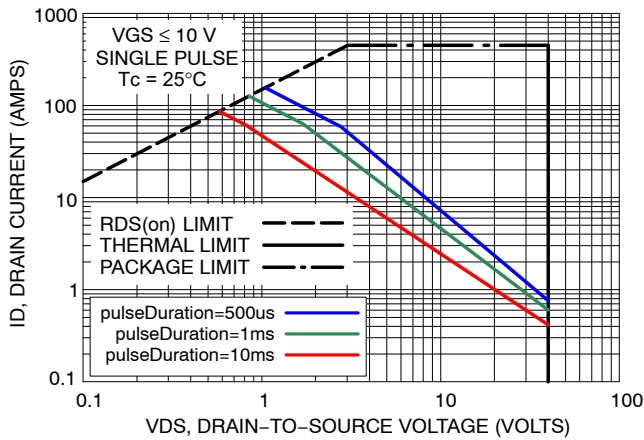


Figure 11. Maximum Rated Forward Biased Safe Operating Area

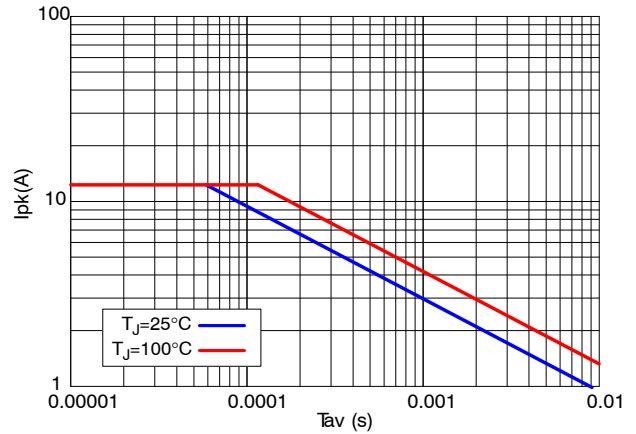


Figure 12. I_{peak} vs. Time in Avalanche

TYPICAL CHARACTERISTICS (continued)

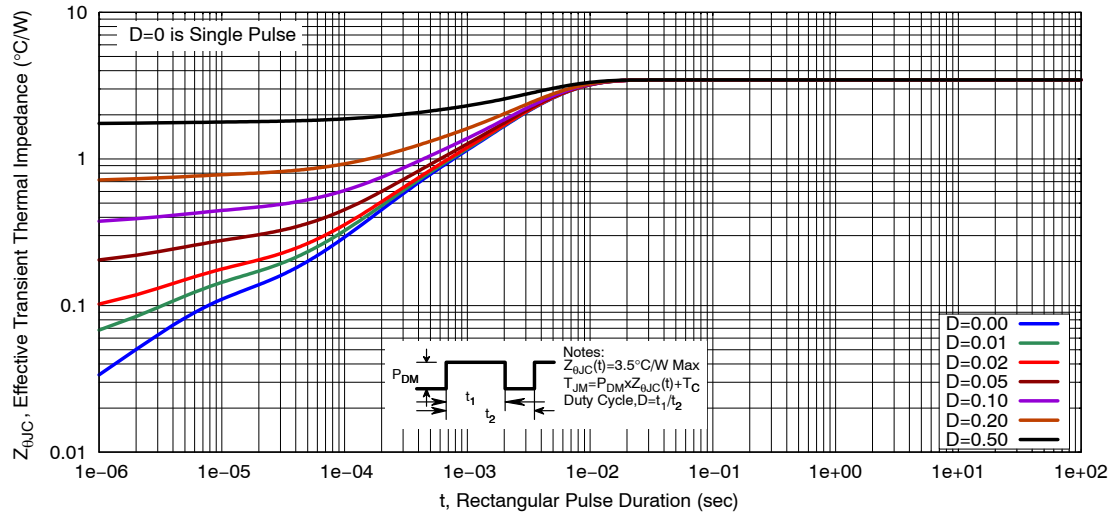


Figure 13. Transient Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFWS4D0N04XMT1G	4D0N4W	DFNW5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

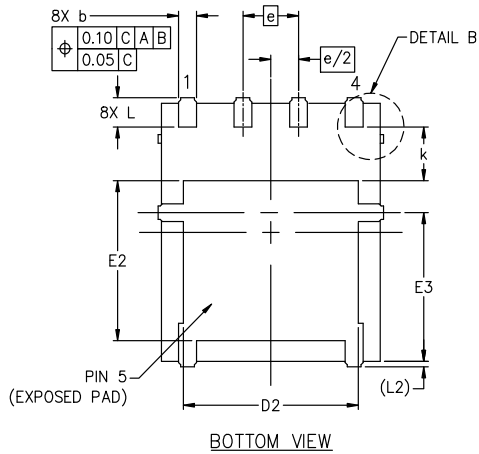
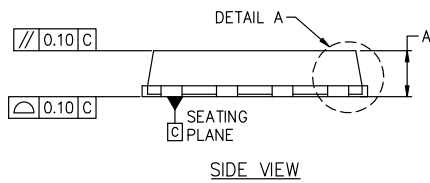
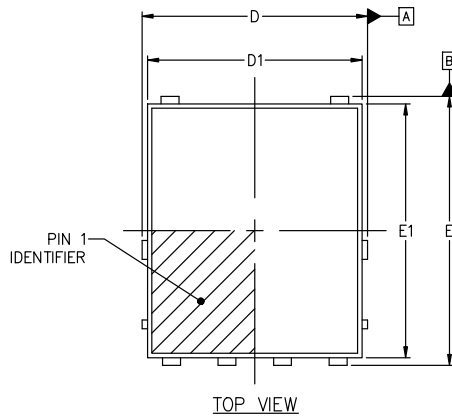
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PACKAGE DIMENSIONS

DFNW5 4.90x5.90x1.00, 1.27P

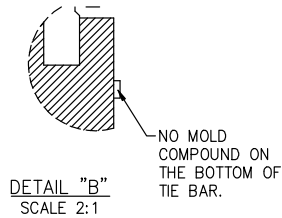
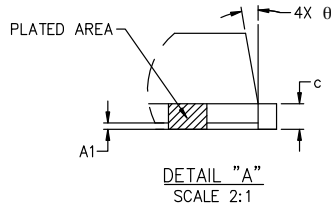
CASE 507BA

ISSUE C

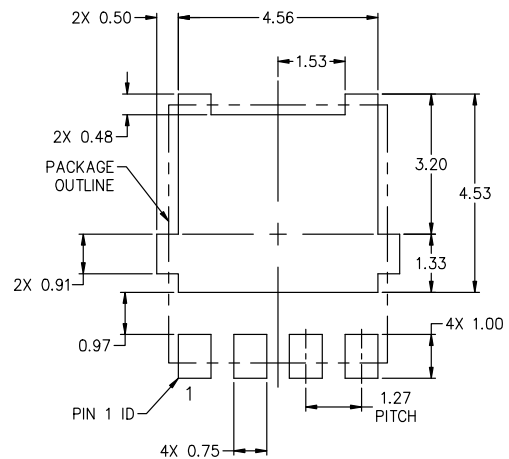


NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
E3	3.00	3.40	3.80
e	1.27 BSC		
k	1.20	1.35	1.50
L	0.51	0.57	0.71
L2	0.15 REF.		
θ	0°	6°	12°



*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

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